

In the Claims:

Please amend the claims as follows:

1.(currently amended) A multilayered substrate for a semiconductor device, ~~which has comprising:~~ a multilayered substrate body formed of a plurality ~~sets~~ of a conductor layers ~~layer~~ and an insulation layers ~~layer~~, and having a face for mounting a semiconductor element thereon and another face for external connection terminals, the face for mounting a semiconductor element ~~device being provided with comprising~~ pads through which the substrate is connected to a the semiconductor element to be mounted thereon, and the face for external connection terminals ~~being provided with comprising~~ pads through which the substrate is connected to an external electrical circuit, wherein a reinforcing sheet is respectively joined to the face for mounting a semiconductor element thereon and the face for external connection terminals of the multilayered substrate body

2.(Canceled)

3.(Canceled)

4.(Canceled)

5.(Original) The multilayered substrate for a semiconductor device of claim 1, wherein the reinforcing sheet joined to the face for external connection terminals is in the form of frame.

6.(Original) The multilayered substrate for a semiconductor device of claim 5, wherein the reinforcing sheet has a reinforcing member or members crossing the inside space of the frame.

7.(Original) The multilayered substrate for a semiconductor device of claim 5, wherein the reinforcing sheet is made of a metal.

8.(Original) The multilayered substrate for a semiconductor device of claim 6, wherein the reinforcing sheet is made of a metal.

9. (Canceled)

10.(Canceled)

11.(Canceled)

12.(currently amended) The multilayered substrate for a semiconductor device of claim 1, 44, wherein the reinforcing sheet joined to the face for mounting a semiconductor element thereon is in the form of a frame made of a metal, and the frame is formed by etching a metal sheet on which the multilayered substrate body is formed so as to remove only the metal material in the region where a semiconductor element is to be mounted.

13.(currently amended) The multilayered substrate for a semiconductor device of claim 1, wherein the pads provided at the face for mounting a semiconductor ~~device~~ element thereon are in the form of bump so that the tip of the pad protrudes from the face for mounting a semiconductor element of the multilayered substrate body.

14.(currently amended) The multilayered substrate for a semiconductor device of claim 2 1, wherein the reinforcing sheet joined to the face for external connection terminals has through holes corresponding to the respective pads for the external connection terminals, and the pads provided at the face for mounting a semiconductor ~~device~~ element thereon are in the form of bump so that the tip of the pad protrudes from the face for mounting a semiconductor element of the multilayered substrate body.

15.(currently amended) The multilayered substrate for a semiconductor device of claim 5, wherein the pads provided at the face for mounting a semiconductor ~~device~~ element thereon are in the form of bump so that the tip of the pad protrudes from the face for mounting a semiconductor element of the multilayered substrate body.

16.(currently amended) The multilayered substrate for a semiconductor device of claim 11, wherein the pads provided at the face for mounting a semiconductor ~~device~~ element thereon are in the form of bump so that the tip of the pad protrudes from the face for mounting a semiconductor element of the multilayered substrate body.

17.(new) A reinforced multilayered substrate for a semiconductor device, the reinforced multilayered substrate comprising:

- a body having a first face side and a second face side;

- a plurality of laminates disposed on at least one face side and overlying one another, each laminate comprising a conductor layer and an insulation layer;

- a plurality of pads, through which the substrate is electrically connectable to a semiconductor element to be mounted thereon, disposed on the outside of the multilayered substrate body on the first face side;

a plurality of external connection terminals, through which the substrate is electrically connectable to an external electrical circuit, disposed on the outside of the multilayered substrate body on the second face side;

a first metal reinforcing layer disposed on the first face side and reinforcingly connected to the a multilayered substrate body, wherein said first metal reinforcing layer comprises openings such as not to prevent access to electrically connect a semiconductor element to the plurality of pads; and

a second reinforcing layer in the form of frame disposed on the second face side and reinforcingly connected to the a multilayered substrate body, wherein said second reinforcing layer comprises openings such as not to prevent access to electrically connect external connection terminals to an external electrical circuit, and has a strength and a coefficient of thermal expansion substantially similar to those of the first metal reinforcing layer,

wherein the reinforced multilayered substrate is substantially flat and unwarped by differences in thermal expansion between layers.

18.(New) The multilayered substrate for a semiconductor device of claim 17, wherein the second reinforcing layer has an insulating surface and has through-holes corresponding to the respective pads for the external connection terminals, and is joined to the second face comprising external connection terminals by an adhesive.

19.(New) The multilayered substrate for a semiconductor device of claim 18, wherein the first reinforcing layer comprises a frame defining an opening, with a region wherein the semiconductor is to be joined to the pads being substantially encompassed by the opening and free of the first reinforcing layer.

20.(New) The multilayered substrate for a semiconductor device of claim 19, wherein the first reinforcing layer comprises a copper frame, and the second reinforcing layer comprises aluminum with an oxide insulating surface, and the adhesive comprises insulating fine particles in an amount sufficient to substantially prevent adhesive from being extruded through the through-holes during manufacture.

21.(New) The multilayered substrate for a semiconductor device of claim 18, wherein the first reinforcing layer comprises a frame defining an opening, with a region wherein the semiconductor is to be joined to the pads being substantially encompassed by the opening, and wherein the first reinforcing layer comprises a reinforcing member or members crossing the inside space of the frame.--